Half-Bridge Driver

Features

- Floating channel designed for bootstrap operation
- Fully operational to +600V
- Tolerant to negative transient voltage
- dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout
- 3.3V, 5V and 15V input logic compatible
- Cross-conduction prevention logic
- Internally set dead-time
- High side output in phase with input
- Shut down input turns off both channels
- Matched propagation delay for both channels

Description

The IR25602 is a high voltage, high speed power MOSFET and IGBT driver with dependent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates from 10 to 600 V.

Product Summary

VOFFSET	600V max.		
I _{O+/-}	130 mA/ 270 mA		
V _{OUT}	10 – 20V		
Ton/off (typ.)	680 & 150 ns		
Dead time (typ.)	520 ns		

Package Options

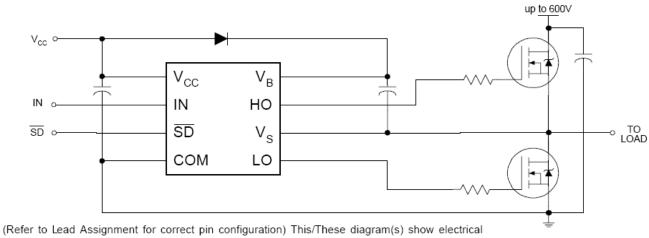


Ordering Information

Dees Deut Neuralean		Standard Pack		Ordershie Bart Number	
Base Part Number	Package Type	Form	Quantity	Orderable Part Number	
IR25602SPBF	SO8N	Tube	95	IR25602SPBF	
IR25602SPBF	SO8N	Tape and Reel	2500	IR25602STRPBF	



Typical Connection Diagram



connections only. Please refer to our Application Notes and DesignTips for proper circuit board layout.



Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units
VB	High side floating absolute voltage	-0.3	625	
VS	High side floating supply offset voltage	V _B - 25	V _B + 0.3	
V _{HO}	High side floating output voltage	V _S - 0.3	V _B + 0.3	V
V _{CC}	Low side and logic fixed supply voltage	-0.3	25	
V _{LO}	Low side output voltage	-0.3	V _{CC} + 0.3	
V _{IN}	Logic input voltage (IN & SD)	-0.3	V _{CC} + 0.3	
dVs/dt	Allowable offset supply voltage transient	—	50	V/ns
PD	Package power dissipation @ $T_A \le +25^{\circ}C$	_	0.625	W
Rth _{JA}	Thermal resistance, junction to ambient	_	200	°C/W
ТJ	Junction temperature	_	150	
Τ _S	Storage temperature	-55	150	°C
TL	Lead temperature (soldering, 10 seconds)	—	300	

Recommended Operating Conditions

For proper operation the device should be used within the recommended conditions. The V_S offset rating is tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
VB	High side floating supply absolute voltage	V _S + 10	V _S + 20	
VS	High side floating supply offset voltage	+	600	
V _{HO}	High side floating output voltage	VS	VB	V
V _{CC}	Low side and logic fixed supply voltage	10	20	
V _{LO}	Low side output voltage	0	V _{CC}	
VIN	Logic input voltage (IN & SD)	0	V _{CC}	
TA	Ambient temperature	-40	125	°C

+Logic operational for VS of -5 to +600V. Logic state held for VS of -5V to -VBS. (Please refer to Design Tip DT97-3 for more details).



Dynamic Electrical Characteristics

 V_{BIAS} (V_{CC}, V_{BS}) = 15V, C_L = 1000 pF and T_A = 25°C unless otherwise specified.

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
t _{on}	Turn-on propagation delay	—	680	820		$V_{\rm S} = 0V$
t _{off}	Turn-off propagation delay	_	150	220		V _S = 600V
t _{sd}	Shutdown propagation delay		160	220		
tr	Turn-on rise time		100	170	ns	
t _f	Turn-off fall time	—	50	90		
DT	Dead time, LS turn-off to HS turn-on & HS turn-on to LS turn-off	400	520	650		
MT	Delay matching, HS & LS turn-on/off	—	—	60		

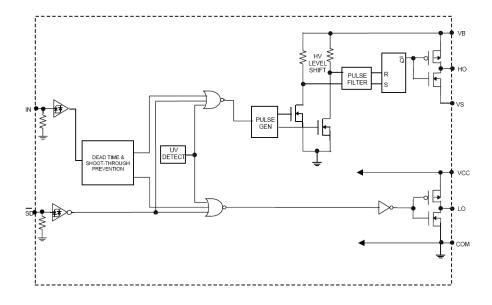
Static Electrical Characteristics

 V_{BIAS} (V_{CC}, V_{BS}) = 15V and T_A = 25°C unless otherwise specified. The V_{IN}, V_{TH} and I_{IN} parameters are referenced to COM. The V_O and I_O parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
V _{IH}	Logic "1" (HO) & Logic "0" (LO) input voltage	3	_	_		V_{CC} = 10V to 20V
VIL	Logic "0" (HO) & Logic "1" (LO) input voltage	_	_	0.8	V	V_{CC} = 10V to 20V
V _{SD,TH+}	SD input positive going threshold	3				V_{CC} = 10V to 20V
V _{SD,TH-}	SD input negative going threshold	—		0.8		V _{CC} = 10V to 20V
V _{OH}	High level output voltage, V _{BIAS} - V _O	_		100	mV	I _O = 0A
V _{OL}	Low level output voltage, V _O	—	_	100		I _O = 0A
I _{LK}	Offset supply leakage current	_	_	50		$V_{B} = V_{S} = 600V$
I _{QBS}	Quiescent V _{BS} supply current	—	30	55		V _{IN} = 0V or 5V
IQCC	Quiescent V _{CC} supply current	—	150	270	μA	V _{IN} = 0V or 5V
I _{IN+}	Logic "1" input bias current	—	3	10		V _{IN} = 5V
I _{IN-}	Logic "0" input bias current	—		1		V _{IN} = 0V
V _{CCUV+}	V _{CC} supply undervoltage positive going threshold	8	8.9	9.8	V	
V _{CCUV-}	V _{CC} supply undervoltage negative going threshold	7.4	8.2	9		
I _{O+}	Output high short circuit pulsed current	130	210	_	mA	V _O = 0V PW ≤ 10 µs
I _{O-}	Output low short circuit pulsed current	270	360			V _O = 15V PW ≤ 10 µs



Functional Block Diagram

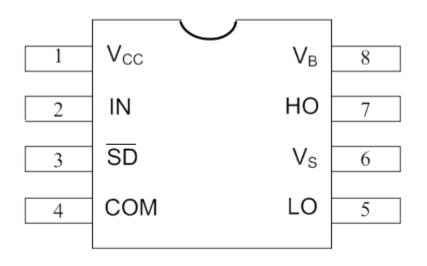




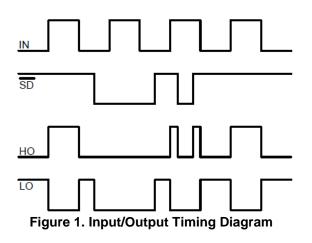
Lead Definitions

Symbol	Description
IN	Logic input for high and low side gate driver outputs (HO and LO), in phase with HO
SD	Logic input for shutdown
VB	High side floating supply
HO	High side gate drive output
VS	High side floating supply return
V _{CC}	Low side and logic fixed supply
LO	Low side gate drive output
COM	Low side return

Lead Assignments



Application Information and Additional Details



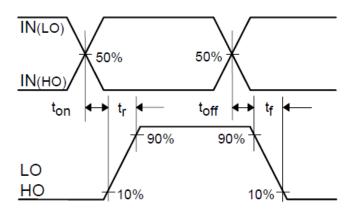


Figure 2. Switching Time Waveform Definitions

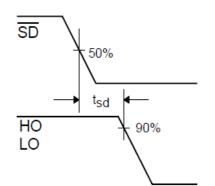
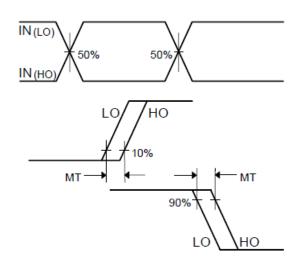


Figure 3. Shutdown Waveform Definitions





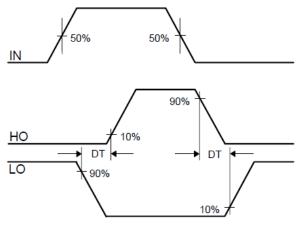


Figure 4. Deadtime Waveform Definitions



20

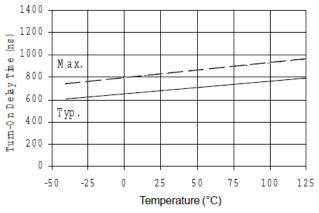
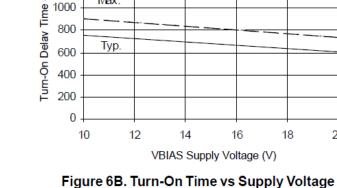


Figure 6A. Turn-On Time vs Temperature



1400

1200 (su)

1000

Max.

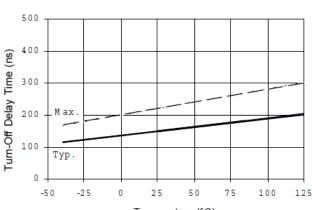




Figure 7A. Turn-Off Time vs Temperature

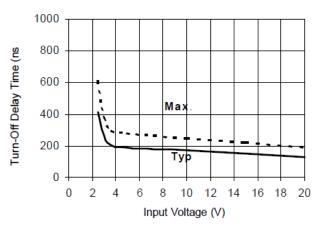
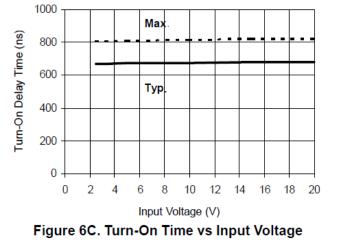


Figure 7C. Turn-Off Time vs Input Voltage



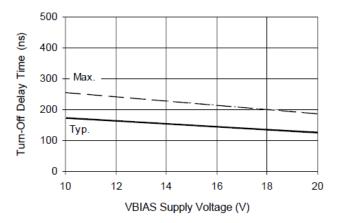


Figure 7B. Turn-Off Time vs Supply Voltage



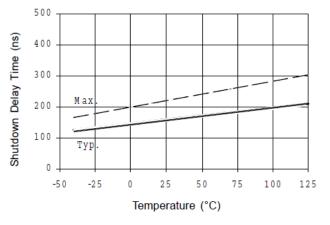
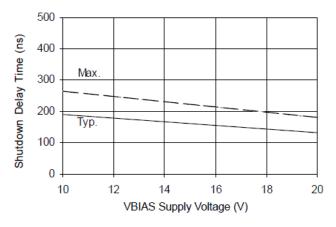
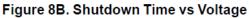
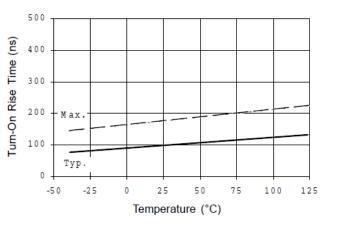
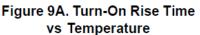


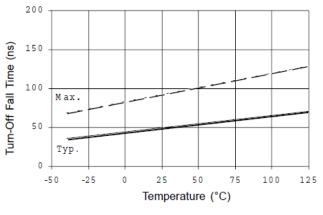
Figure 8A. Shutdown Time vs Temperature

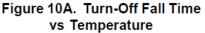












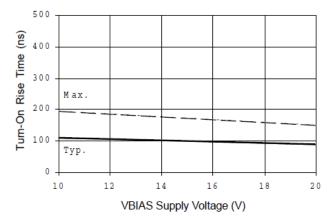


Figure 9B. Turn-On Rise Time vs Voltage

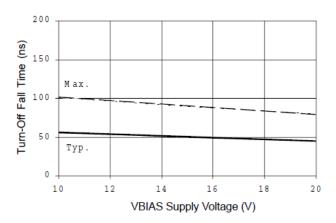


Figure 10B. Turn-Off Fall Time vs Voltage



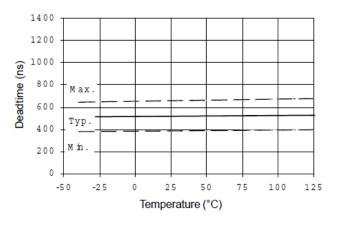
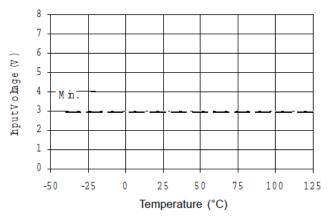
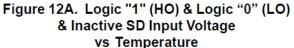
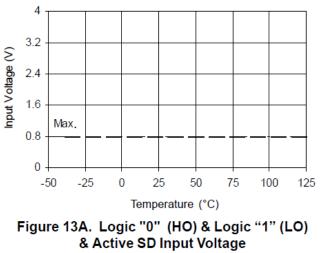
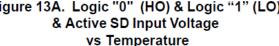


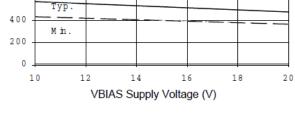
Figure 11A. Deadtime vs Temperature











1400

1200

1000

800

600

Max.

Deadtime (ns)

Figure 11B. Deadtime vs Voltage

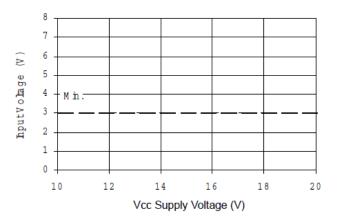


Figure 12B. Logic "1" (HO) & Logic "0" (LO) & Inactive SD Input Voltage vs Voltage

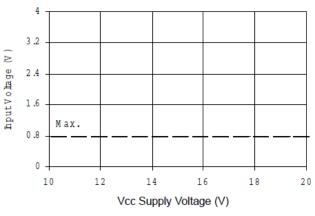
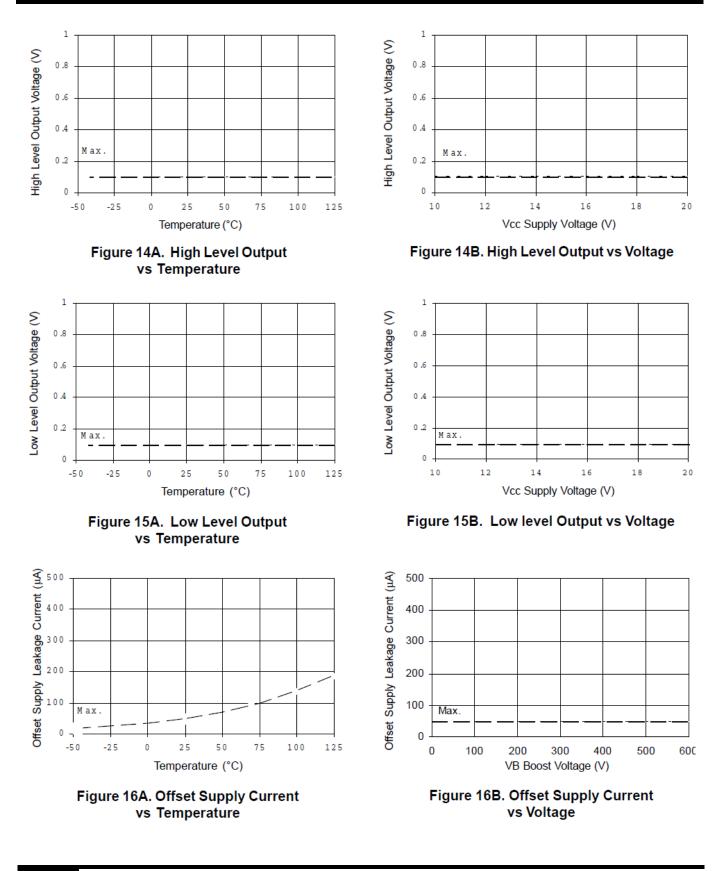
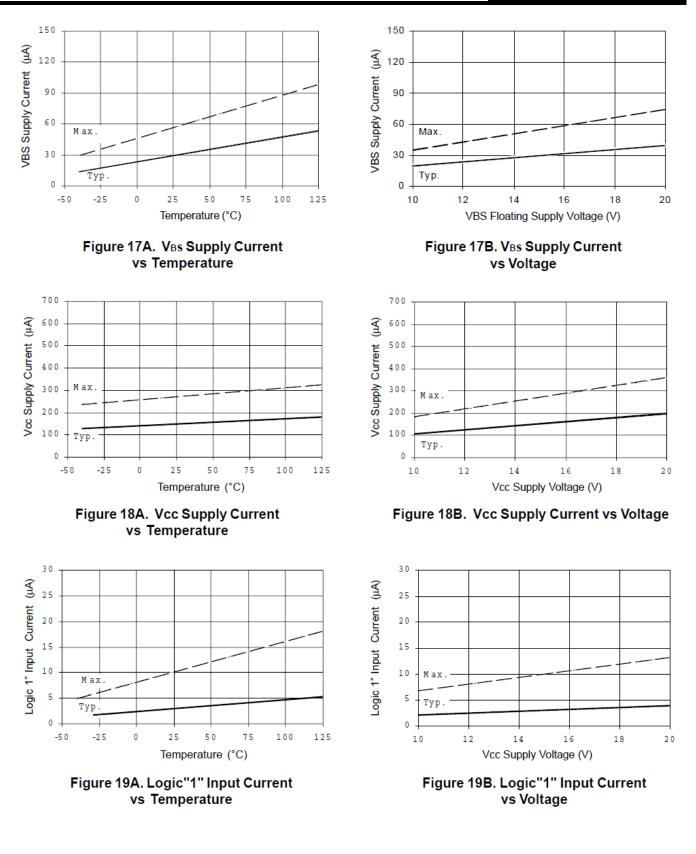


Figure 13B. Logic "0" (HO) & Logic "1" (LO) & Active SD Input Voltage vs Voltage

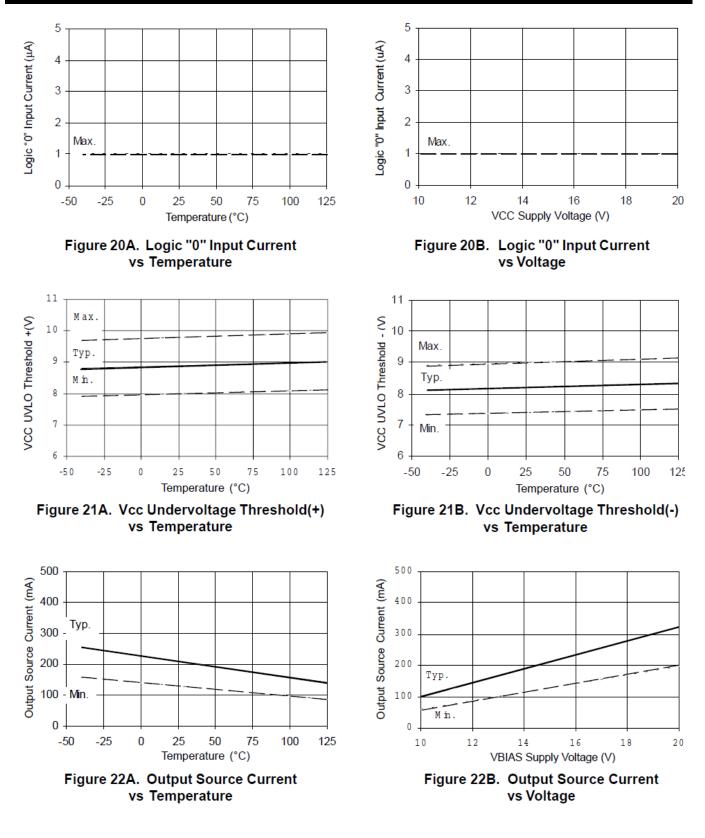




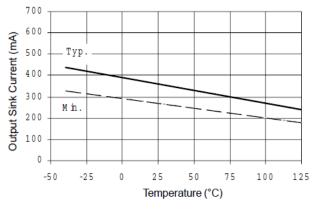


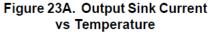












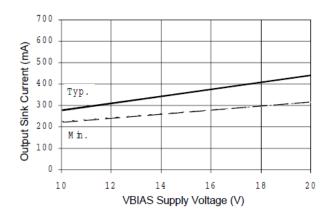
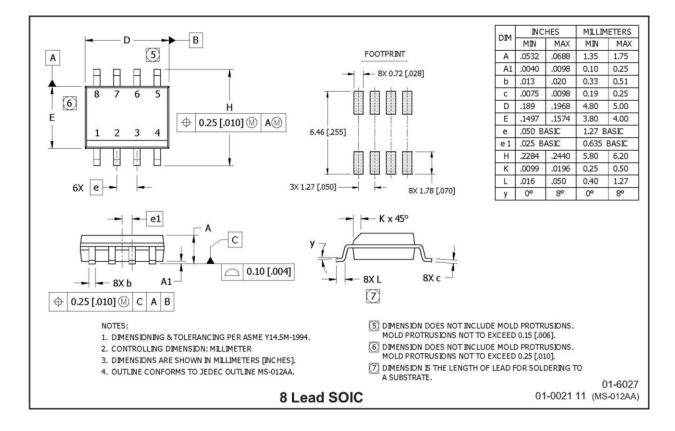


Figure 23B. Output Sink Current vs Voltage

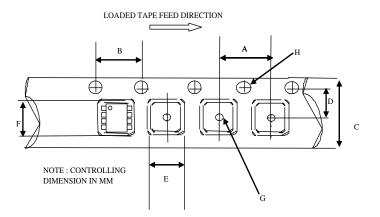


Package Details



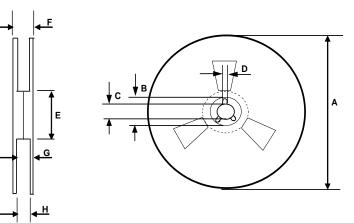


Tape and Reel Details



CARRIER TAPE DIMENSION FOR 8SOICN

	Metric		Imp	erial
Code	Min	Max	Min	Max
A	7.90	8.10	0.311	0.318
В	3.90	4.10	0.153	0.161
С	11.70	12.30	0.46	0.484
D	5.45	5.55	0.214	0.218
E	6.30	6.50	0.248	0.255
F	5.10	5.30	0.200	0.208
G	1.50	n/a	0.059	n/a
Н	1.50	1.60	0.059	0.062

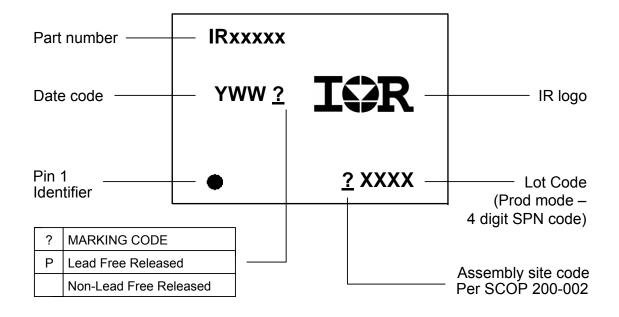


REEL DIMENSIONS FOR 8SOICN

	Me	etric	Imperial		
Code	Min	Max	Min	Max	
A	329.60	330.25	12.976	13.001	
В	20.95	21.45	0.824	0.844	
С	12.80	13.20	0.503	0.519	
D	1.95	2.45	0.767	0.096	
E	98.00	102.00	3.858	4.015	
F	n/a	18.40	n/a	0.724	
G	14.50	17.10	0.570	0.673	
Н	12.40	14.40	0.488	0.566	



Part Marking Information



Qualification Information[†]

	Industrial ^{††}		
	(per JEDEC JESD 47)		
Qualification Level	Comments: This family of ICs has passed JEDEC's		
	Industrial qualification. IR's Consumer qualification level is		
	granted by extension of the higher Industrial level.		
Moisture Sensitivity Level	MSL2 ^{†††}		
Moisture Sensitivity Level	(per IPC/JEDEC J-STD-020)		
RoHS Compliant	Yes		

- † Qualification standards can be found at International Rectifier's web site http://www.irf.com/
- ++ Higher qualification ratings may be available should the user have such requirements. Please contact your International Rectifier sales representative for further information.
- +++ Higher MSL ratings may be available for the specific package types listed here. Please contact your International Rectifier sales representative for further information.

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